

Nonvolatile Memories Based on Graphene and Related 2

Advanced Materials

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Scanning near-field optical microscopy based phase-change optical memory. Applied Physics Express, 2019, 12, 095002.	1.1	1
2	Modulating the Charge Transport in 2D Semiconductors via Energyâ€Level Phototuning. Advanced Materials, 2019, 31, 1903402.	11.1	30
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6	Non-equilibrium processing of ferromagnetic heavily reduced graphene oxide. Carbon, 2019, 153, 663-673.	5.4	15
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18	GaSe layered nanorods formed by liquid phase exfoliation for resistive switching memory applications. Journal of Alloys and Compounds, 2020, 823, 153697.	2.8	9

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20	Artificial synapses with photoelectric plasticity and memory behaviors based on charge trapping memristive system. <i>Materials and Design</i> , 2020, 188, 108415.	3.3	41
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